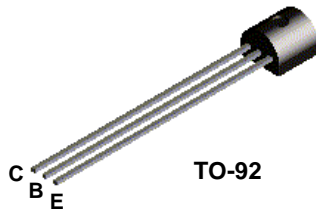


PN4356



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 67. See TN4033A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	1.0	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN4356	
P_D	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier

(continued)

PN4356

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	80		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	80		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$ $V_{CB} = 50 \text{ V}, I_E = 0, T_A = 75 \text{ }^\circ\text{C}$		50 5.0	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$ $V_{EB} = 4.0 \text{ V}, I_C = 0$		10 100	μA nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_C = 100 \text{ } \mu\text{A}$ $V_{CE} = 10 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 100 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	25 40 50 40 30	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.15 0.50	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.90 1.10	V V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz}$		30	pF
C_{ib}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		110	pF
h_{fe}	Small-Signal Current Gain	$I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	1.0	5.0	
NF	Noise Figure	$V_{CE} = 10 \text{ V}, I_C = 100 \text{ } \mu\text{A},$ $R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_W = 1.0 \text{ Hz}$		3.0	dB

SWITCHING CHARACTERISTICS

t_{on}	Turn-on Time	$V_{CC} = 30 \text{ V}, I_C = 500 \text{ mA},$		100	ns
t_{off}	Turn-off Time	$I_{B1} = I_{B2} = 50 \text{ mA}$		400	ns

* Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 2.0\%$